III-Nitride Tunnel Junction LED with High Wall Plug Efficiency

Tech ID: 31762 / UC Case 2017-131-0

BACKGROUND

Commercially-available III-nitride light-emitting diodes (LEDs) use an active region in a biased p-n junction to allow for electron and hole injection. The p-GaN is difficult to contact electrically and has low hole concentration and mobility. This means that p-GaN cannot be used as a current spreading layer and that traditional p-contacts will add significant voltage to devices. Despite these inherent problems, all commercial light emitting devices utilize a p-contact and a material other than p-GaN for current spreading, typically transparent conducting oxides (TCO).

DESCRIPTION

Researchers at the University of California, Santa Barbara have introduced an n-GaN layer that produces less loss than a traditional transparent conducting oxide. The favorable current spreading of the n-GaN layer also helps to reduce the droop observed in previous iterations of III-Nitride LEDs. The combined benefits of this novel current spreading layer materialize into a device with over 70% wall plug efficiency.

ADVANTAGES

- Improved light extraction
- Improved energy efficiency (over 70%)
- No requirement for TCOs or mirrors

APPLICATIONS

- III-Nitride LEDs

PATENT STATUS

Country	Type	Number	Dated	Case
United States Of America	Issued Patent	11,164,997	11/02/2021	2017-131

RELATED TECHNOLOGIES

- Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation

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OTHER INFORMATION

KEYWORDS

LED, tunnel junction, GaN, III-nitride LED

CATEGORIZED AS

- **Energy**
  - Lighting
- **Semiconductors**
  - Design and Fabrication

RELATED CASES

2017-131-0

- Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- III-Nitride-Based Vertical Cavity Surface Emitting Laser (VCSEL) with a Dielectric P-Side Lens
- Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- Methods to Produce and Recycle Substates for III-Nitride Materials with Electrochemical Etching
- Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- Thermally Stable, Laser-Driven White Lighting Device
- Novel Multilayer Structure for High-Efficiency UV and Far-UV Light-Emitting Devices
- A Method To Lift-Off Nitride Materials With Electrochemical Etch
- High-Intensity Solid State White Laser Diode
- Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- A Wafer-Scale, Low Defect Density Strain Relaxed Template for III-Nitride-Based High Efficiency and High-Power Devices
- High-Efficiency and High-Power III-Nitride Devices Grown on or Above a Strain Relaxed Template
- III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture

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